

Abstract of Disclosure

5

METHOD FOR FABRICATING TRANSISTOR

10 A method for fabricating a transistor utilizes gate shadow effect. A gate electrode is provided on a main surface of a semiconductor substrate. A drain-forming region on one side of the gate electrode is masked with a first photoresist pattern. A first lightly doped drain (LDD) implant is performed with a tilt angle to dope a source-forming region on the other side of the gate electrode, thereby forming a first LDD region therein. The first photoresist pattern is then stripped. The
15 source-forming region is masked with a second photoresist pattern. A second LDD implant is performed with the tilt angle to dope the drain-forming region, thereby forming a second LDD region therein.

20 Figure 2